

TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

2SK3376TV

For ECM

- Application for Ultra-compact ECM

Absolute Maximum Ratings (Ta=25°C)

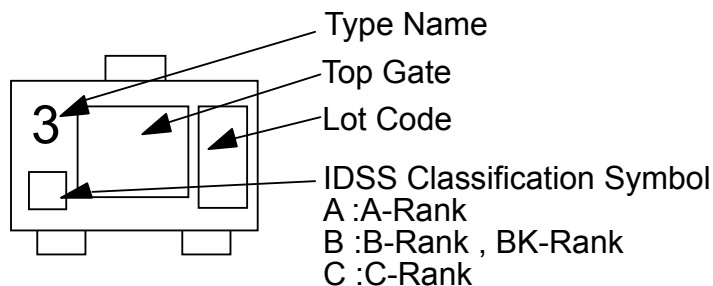
Characteristic	Symbol	Rating	Unit
Gate-Drain voltage	V _{GDO}	-20	V
Gate Current	I _G	10	mA
Drain power dissipation (Ta = 25°C)	P _D	100	mW
Junction Temperature	T _j	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

IDSS CLASSIFICATION

A-Rank	80 to 200μA
B-Rank	170 to 300μA
C-Rank	270 to 480μA
BK-Rank	150 to 350μA

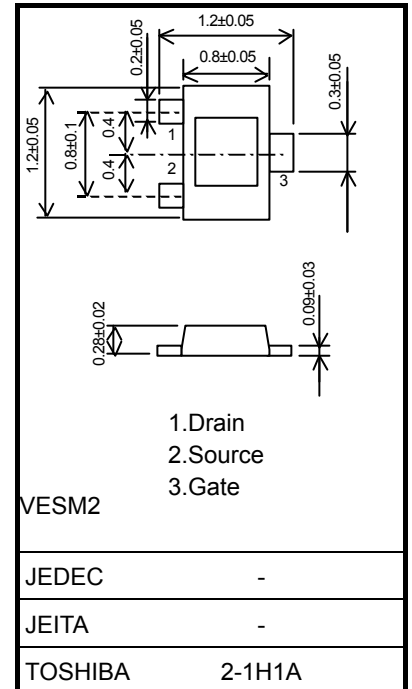
Marking



Precaution

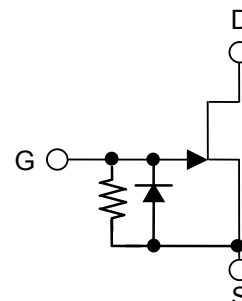
There is a metal plate on the top of package, which has the same electrical potential as the Gate terminal. Don't use it as a terminal.

Unit: mm



Weight: 0.8mg (typ.)

Equivalent Circuit



Electrical Characteristics (A-Rank IDSS Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Drain Current	I _{DSS}	V _{DS} = 2 V, V _{GS} = 0	80	—	200	μA
Drain Current	I _D	V _{DD} = 2 V, RL = 2kΩ, Cg = 3pF	—	—	240	μA
Gate-Source Cut-off Voltage	V _{GS(OFF)}	V _{DS} = 2 V, I _D = 1μA	-0.1	—	-0.8	V
Forward transfer admittance	Y _{fs}	V _{DS} = 2 V, V _{GS} = 0V	0.7	1.4	—	mS
Input capacitance	C _{iss}	V _{DS} = 2 V, V _{GS} = 0, f = 1 MHz	—	5.5	—	pF
Voltage Gain	G _v	V _{DD} = 2V, RL = 2kΩ, Cg = 3pF, f = 1kHz	-13.5	—	-9.0	dB
Delta Voltage Gain	DG _{v(f)}	V _{DD} = 2V, RL = 2kΩ, Cg = 3pF, f = 1kHz to 100Hz	—	—	-2.0	dB
Delta Voltage Gain	DG _{v(V)}	V _{DD} = 2V to 1V, RL = 2kΩ, Cg = 3pF, f = 1kHz	—	—	-4.0	dB
Noise Voltage	V _N	V _{DD} = 2V, RL = 1kΩ, Cg = 3pF, G _v = 80dB, f = A-Curve Filter	—	—	47	mV

Electrical Characteristics (B-Rank IDSS Ta=25°C)

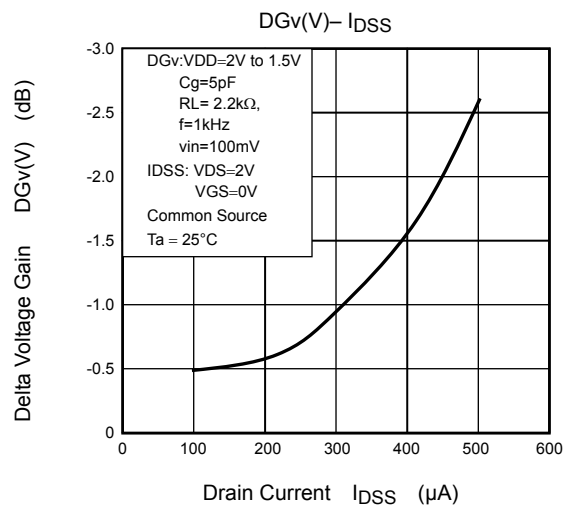
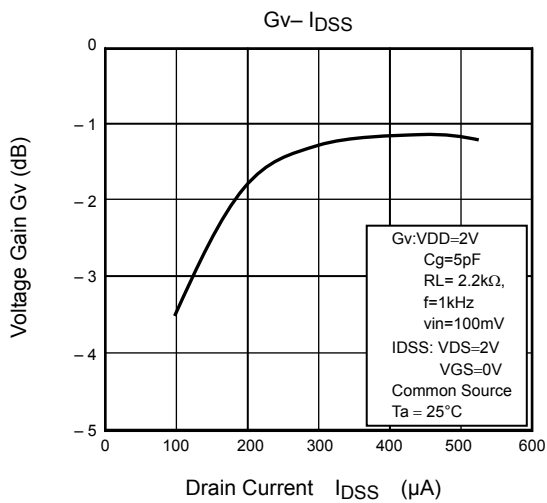
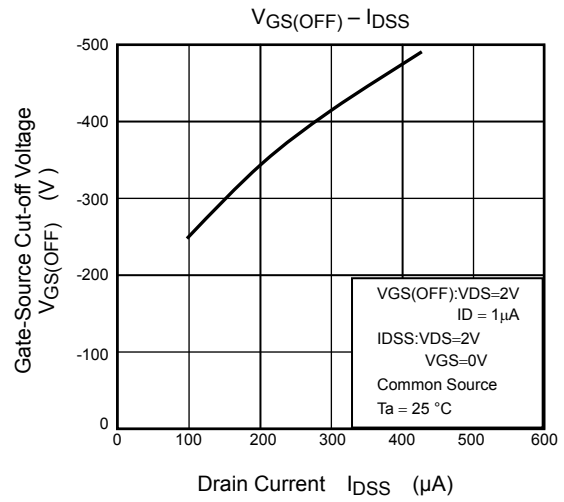
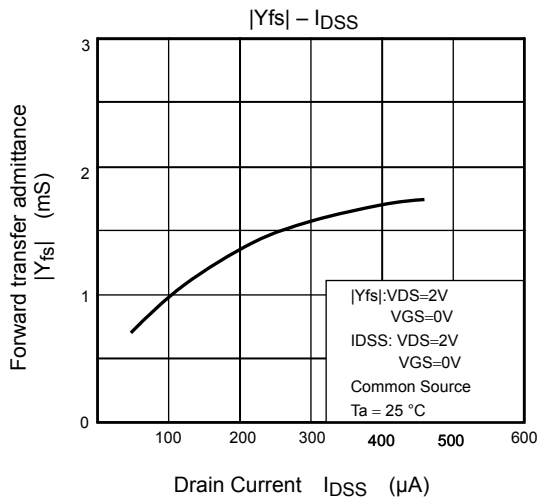
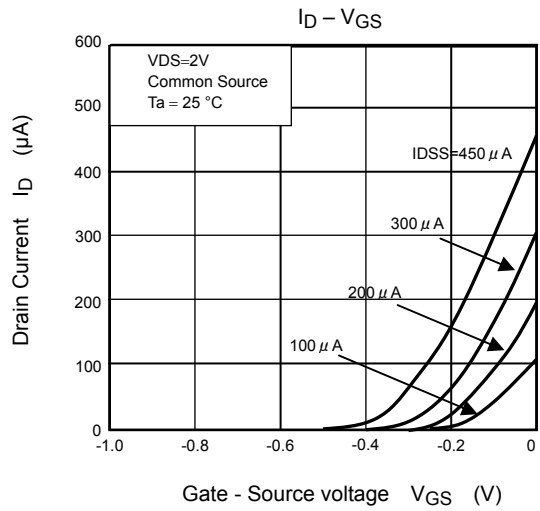
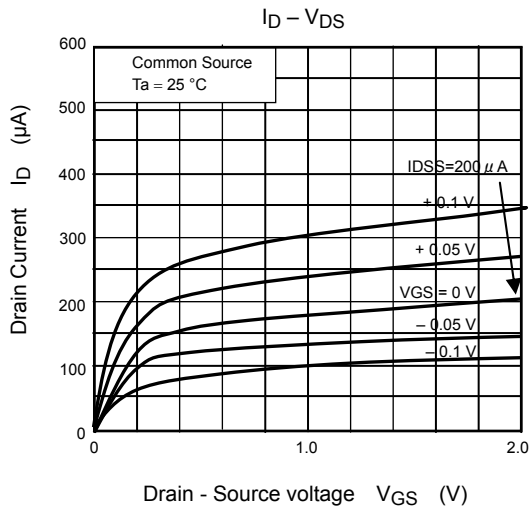
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Drain Current	I _{DSS}	V _{DS} = 2 V, V _{GS} = 0	170	—	300	μA
Drain Current	I _D	V _{DD} = 2 V, RL = 2kΩ, Cg = 3pF	—	—	340	μA
Gate-Source Cut-off Voltage	V _{GS(OFF)}	V _{DS} = 2 V, I _D = 1μA	-0.15	—	-1.0	V
Forward transfer admittance	Y _{fs}	V _{DS} = 2 V, V _{GS} = 0V	0.7	1.4	—	mS
Input capacitance	C _{iss}	V _{DS} = 2 V, V _{GS} = 0, f = 1 MHz	—	5.5	—	pF
Voltage Gain	G _v	V _{DD} = 2V, RL = 2kΩ, Cg = 3pF, f = 1kHz	-11.5	—	-8.0	dB
Delta Voltage Gain	DG _{v(f)}	V _{DD} = 2V, RL = 2kΩ, Cg = 3pF, f = 1kHz to 100Hz	—	—	-2.0	dB
Delta Voltage Gain	DG _{v(V)}	V _{DD} = 2V to 1V, RL = 2kΩ, Cg = 3pF, f = 1kHz	—	—	-7.0	dB
Noise Voltage	V _N	V _{DD} = 2V, RL = 1kΩ, Cg = 3pF, G _v = 80dB, f = A-Curve Filter	—	—	50	mV

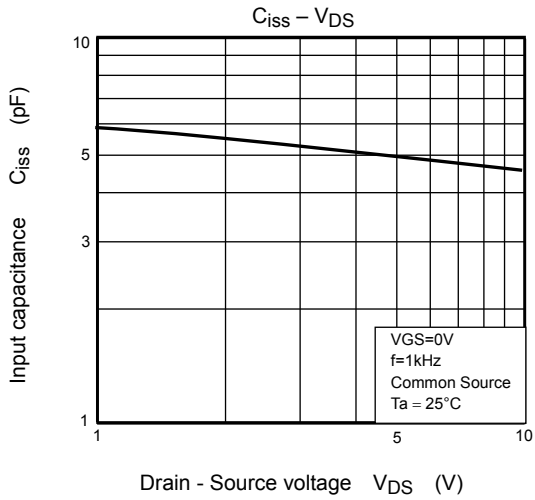
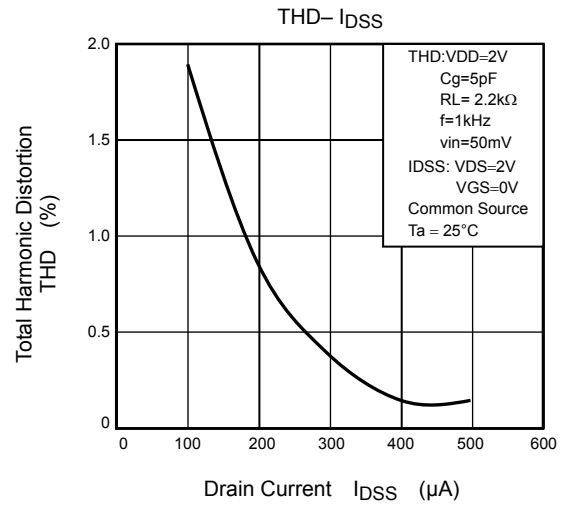
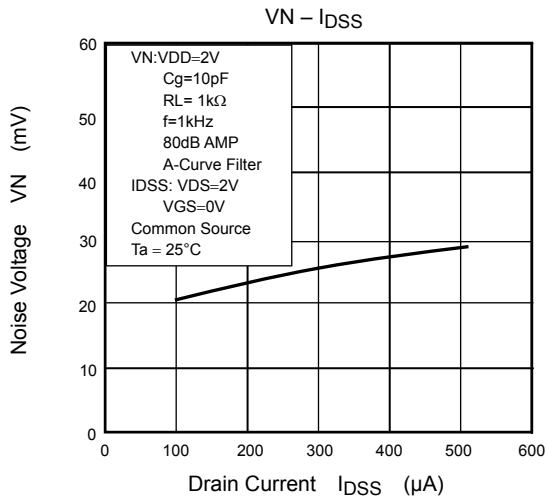
Electrical Characteristics (C-Rank IDSS Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Drain Current	I _{DSS}	V _{DS} = 2 V, V _{GS} = 0	270	—	480	μA
Drain Current	I _D	V _{DD} = 2 V, RL = 2kΩ, Cg = 3pF	—	—	520	μA
Gate-Source Cut-off Voltage	V _{GS(OFF)}	V _{DS} = 2 V, I _D = 1μA	-0.2	—	-1.2	V
Forward transfer admittance	Y _{fs}	V _{DS} = 2 V, V _{GS} = 0V	0.7	1.4	—	mS
Input capacitance	C _{iss}	V _{DS} = 2 V, V _{GS} = 0, f = 1 MHz	—	5.5	—	pF
Voltage Gain	G _v	V _{DD} = 2V, RL = 2kΩ, Cg = 3pF, f = 1kHz	-10.5	—	-6.75	dB
Delta Voltage Gain	DG _{v(f)}	V _{DD} = 2V, RL = 2kΩ, Cg = 3pF, f = 1kHz to 100Hz	—	—	-2.0	dB
Delta Voltage Gain	DG _{v(V)}	V _{DD} = 2V to 1V, RL = 2kΩ, Cg = 3pF, f = 1kHz	—	—	-20	dB
Noise Voltage	V _N	V _{DD} = 2V, RL = 1kΩ, Cg = 3pF, G _v = 80dB, f = A-Curve Filter	—	—	75	mV

Electrical Characteristics (BK-Rank IDSS Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Drain Current	I_{DSS}	$V_{DS} = 2\text{ V}, V_{GS} = 0$	150	—	350	μA
Drain Current	I_D	$V_{DD} = 2\text{ V}, R_L = 2\text{ k}\Omega, C_g = 3\text{ pF}$	—	—	390	μA
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$	$V_{DS} = 2\text{ V}, I_D = 1\mu\text{A}$	-0.125	—	-1.1	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 2\text{ V}, V_{GS} = 0\text{ V}$	0.7	1.4	—	mS
Input capacitance	C_{iss}	$V_{DS} = 2\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	5.5	—	pF
Voltage Gain	G_v	$V_{DD} = 2\text{ V}, R_L = 2\text{ k}\Omega, C_g = 3\text{ pF}, f = 1\text{ kHz}$	-12.0	—	-7.50	dB
Delta Voltage Gain	$DG_v(f)$	$V_{DD} = 2\text{ V}, R_L = 2\text{ k}\Omega, C_g = 3\text{ pF}, f = 1\text{ kHz to } 100\text{ Hz}$	—	—	-2.0	dB
Delta Voltage Gain	$DG_v(V)$	$V_{DD} = 2\text{ V to } 1\text{ V}, R_L = 2\text{ k}\Omega, C_g = 3\text{ pF}, f = 1\text{ kHz}$	—	—	-13.5	dB
Noise Voltage	V_N	$V_{DD} = 2\text{ V}, R_L = 1\text{ k}\Omega, C_g = 3\text{ pF}, G_v = 80\text{ dB}, f = \text{A-Curve Filter}$	—	—	65	mV





RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

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